

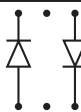
CMLD6263DO

**SURFACE MOUNT  
DUAL OPPOSING  
HIGH VOLTAGE  
SILICON SCHOTTKY DIODES**



[www.centrasemi.com](http://www.centrasemi.com)

PICOmini™



SOT-563 CASE

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMLD6263DO incorporates two galvanically isolated, High Voltage, low  $V_F$  Silicon Diodes with an opposing Anode/Cathode configuration, in a space saving SOT-563 surface mount package. These diodes are designed for fast switching applications requiring a low forward voltage drop.

**MARKING CODE: 630**

**FEATURES:**

- Dual Opposing (DO) Schottky Diodes
- High Voltage (70V)
- Low Forward Voltage
- Galvanically Isolated

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	$V_{RRM}$	70	V
Continuous Forward Current	$I_F$	15	mA
Peak Forward Surge Current, $t_p=1.0\text{s}$	$I_{FSM}$	50	mA
Power Dissipation	$P_D$	250	mW
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
Thermal Resistance	$\theta_{JA}$	500	$^\circ\text{C/W}$

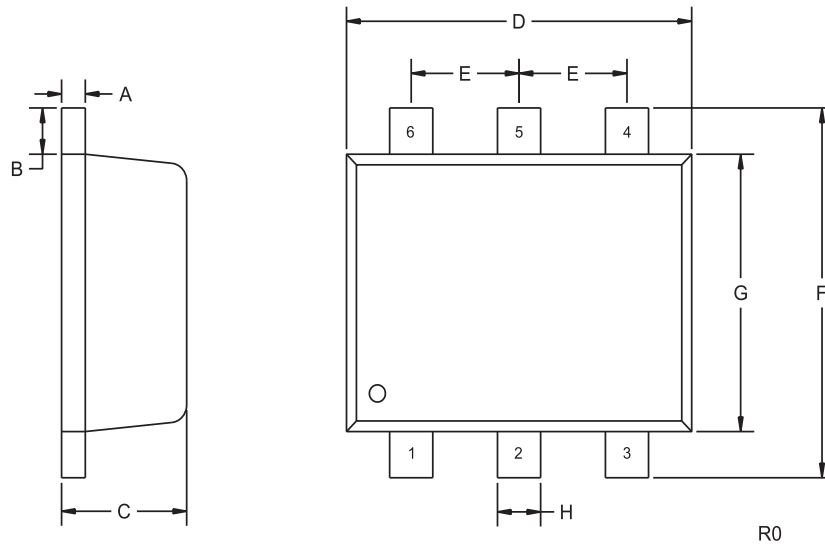
**ELECTRICAL CHARACTERISTICS PER DIODE:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_R$	$V_R=50\text{V}$		98	200	nA
$BV_R$	$I_R=10\mu\text{A}$	70			V
$V_F$	$I_F=1.0\text{mA}$		395	410	mV
$C_T$	$V_R=0, f=1.0\text{MHz}$			2.0	pF
$t_{rr}$	$I_R=I_F=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

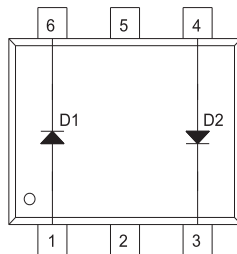
**CMLD6263DO**  
**SURFACE MOUNT**  
**DUAL OPPOSING**  
**HIGH VOLTAGE**  
**SILICON SCHOTTKY DIODES**



**SOT-563 CASE - MECHANICAL OUTLINE**



**PIN CONFIGURATION**



**LEAD CODE:**

- 1) Anode D1
- 2) NC
- 3) Cathode D2
- 4) Anode D2
- 5) NC
- 6) Cathode D1

**MARKING CODE: 630**

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

R3 (18-January 2010)